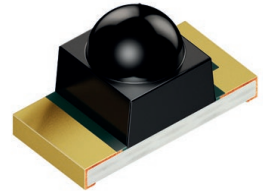


# SFH 4059SR

## Chip LED Lens

High Power Infrared Emitter (850 nm)



## Applications

- Electronic Equipment

## Features:

- Package: black epoxy
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)
- High optical power
- Double stack emitter
- Very small SMT package
- Reverse mount

## Ordering Information

| Type          | Irradiance <sup>1)2)</sup><br>$I_F = 50 \text{ mA}; t_p = 20 \text{ ms}$<br>$E_e$ | Irradiance <sup>1)</sup><br>typ.<br>$I_F = 50 \text{ mA}; t_p = 20 \text{ ms}$<br>$E_e$ | Ordering Code |
|---------------|-----------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------|---------------|
| SFH 4059SR    | 7.1 ... 28.0 mW/cm <sup>2</sup>                                                   | 16 mW/cm <sup>2</sup>                                                                   | Q65111A5310   |
| SFH 4059SR-RS | 11.2 ... 28.0 mW/cm <sup>2</sup>                                                  | 16 mW/cm <sup>2</sup>                                                                   | Q65111A7313   |

$E_e$  measured in the near field with a detector (7.2 mm diameter) in 20 mm distance ( $\Omega = 0.1 \text{ sr}$ ) to the device surface

## Maximum Ratings

$T_A = 25\text{ °C}$

| Parameter                                                                    | Symbol               |              | Values          |
|------------------------------------------------------------------------------|----------------------|--------------|-----------------|
| Operating temperature                                                        | $T_{op}$             | min.<br>max. | -40 °C<br>85 °C |
| Storage temperature                                                          | $T_{stg}$            | min.<br>max. | -40 °C<br>85 °C |
| Forward current                                                              | $I_F$                | max.         | 50 mA           |
| Forward current pulsed<br>$t_p \leq 300\text{ }\mu\text{s}$ ; $D \leq 0.005$ | $I_{F\text{ pulse}}$ | max.         | 0.7 A           |
| Reverse voltage <sup>3)</sup>                                                | $V_R$                | max.         | 5 V             |
| Power consumption                                                            | $P_{tot}$            | max.         | 175 mW          |
| ESD withstand voltage<br>acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)       | $V_{ESD}$            | max.         | 2 kV            |

## Characteristics

$I_F = 50 \text{ mA}$ ;  $t_p = 20 \text{ ms}$ ;  $T_A = 25 \text{ °C}$

| Parameter                                                                   | Symbol                      |              | Values                                 |
|-----------------------------------------------------------------------------|-----------------------------|--------------|----------------------------------------|
| Peak wavelength                                                             | $\lambda_{\text{peak}}$     | typ.         | 860 nm                                 |
| Centroid wavelength                                                         | $\lambda_{\text{centroid}}$ | typ.         | 850 nm                                 |
| Spectral bandwidth at 50% $I_{\text{rel,max}}$ (FWHM)                       | $\Delta\lambda$             | typ.         | 30 nm                                  |
| Half angle                                                                  | $\varphi$                   | typ.         | 15 °                                   |
| Dimensions of active chip area                                              | L x W                       | typ.         | 0.3 x 0.3 mm x mm                      |
| Rise time (10% / 90%)<br>$I_F = 50 \text{ mA}$ ; $R_L = 50 \text{ }\Omega$  | $t_r$                       | typ.         | 15 ns                                  |
| Fall time (10% / 90%)<br>$I_F = 50 \text{ mA}$ ; $R_L = 50 \text{ }\Omega$  | $t_f$                       | typ.         | 15 ns                                  |
| Forward voltage <sup>4)</sup>                                               | $V_F$                       | typ.<br>max. | 2.95 V<br>3.35 V                       |
| Forward voltage<br>$I_F = 700 \text{ mA}$ ; $t_p = 100 \text{ }\mu\text{s}$ | $V_F$                       | typ.         | 4 V                                    |
| Reverse current <sup>3)</sup><br>$V_R = 5 \text{ V}$                        | $I_R$                       | typ.<br>max. | 0.01 $\mu\text{A}$<br>10 $\mu\text{A}$ |
| Radiant intensity <sup>5)</sup>                                             | $I_e$                       | typ.         | 95 mW/sr                               |
| Total radiant flux <sup>6)</sup>                                            | $\Phi_e$                    | typ.         | 50 mW                                  |
| Temperature coefficient of voltage                                          | $TC_V$                      | typ.         | -2 mV / K                              |
| Temperature coefficient of brightness                                       | $TC_I$                      | typ.         | -0.5 % / K                             |
| Temperature coefficient of wavelength                                       | $TC_\lambda$                | typ.         | 0.3 nm / K                             |
| Thermal resistance junction solder point real <sup>7)</sup>                 | $R_{\text{thJS real}}$      | max.         | 260 K / W                              |
| Thermal resistance junction ambient real <sup>8)</sup>                      | $R_{\text{thJA}}$           | max.         | 420 K / W                              |

Radiant Intensity measured with a detector (11.3 mm diameter) in 100 mm distance ( $\Omega = 0.01 \text{ sr}$ ) to the device surface

## Brightness Groups

$T_A = 25\text{ °C}$

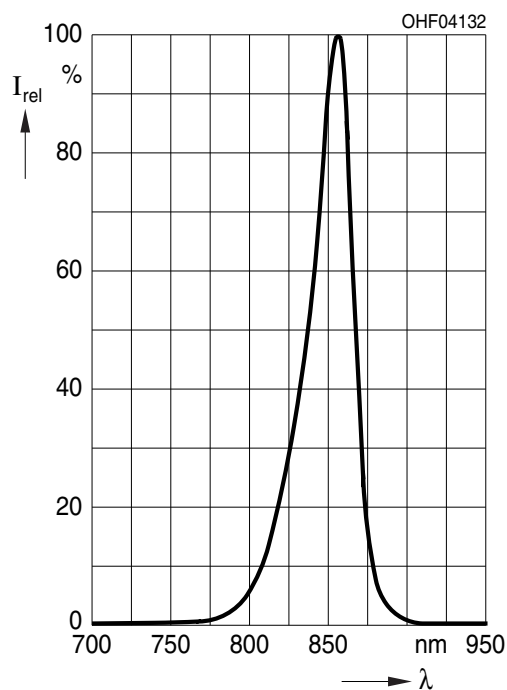
| Group | Irradiance <sup>1)2)</sup><br>$I_F = 50\text{ mA}; t_p = 20\text{ ms}$<br>min.<br>$E_e$ | Irradiance <sup>1)2)</sup><br>$I_F = 50\text{ mA}; t_p = 20\text{ ms}$<br>max.<br>$E_e$ |
|-------|-----------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------|
|       |                                                                                         |                                                                                         |
| Q     | 7.1 mW/cm <sup>2</sup>                                                                  | 11.2 mW/cm <sup>2</sup>                                                                 |
| R     | 11.2 mW/cm <sup>2</sup>                                                                 | 18.0 mW/cm <sup>2</sup>                                                                 |
| S     | 18.0 mW/cm <sup>2</sup>                                                                 | 28.0 mW/cm <sup>2</sup>                                                                 |

Only one group in one packing unit (variation lower 2:1).

$E_e$  measured in the near field with a detector (7.2 mm diameter) in 20 mm distance ( $\Omega = 0.1\text{ sr}$ ) to the device surface

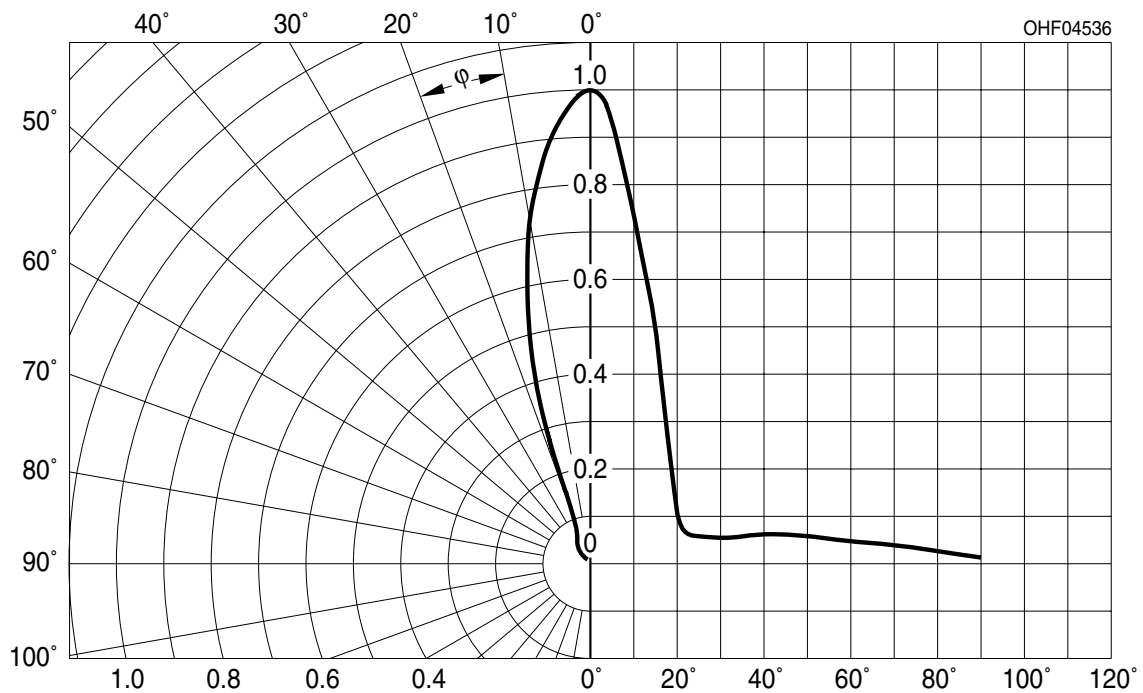
## Relative Spectral Emission <sup>9), 10)</sup>

$I_{e,rel} = f(\lambda); I_F = 50\text{ mA}; t_p = 20\text{ ms}$



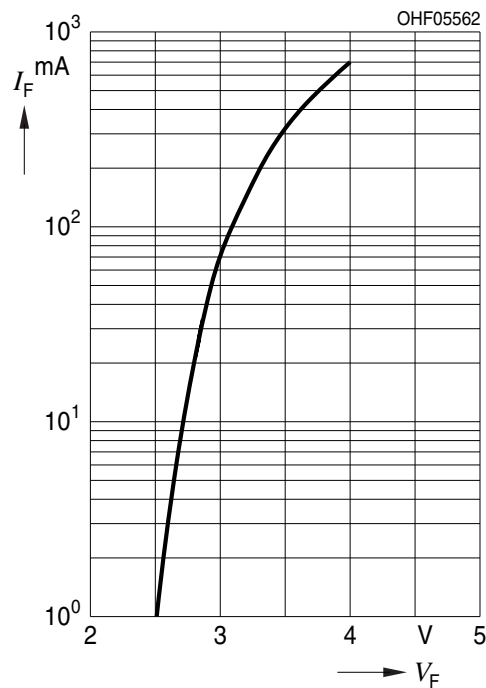
## Radiation Characteristics 9), 10)

$$I_{e,rel} = f(\varphi)$$



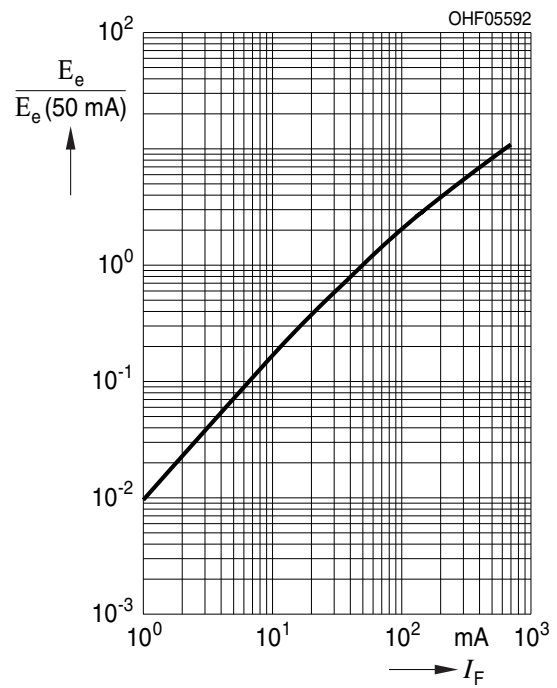
## Forward current 9), 10)

$$I_F = f(V_F); \text{ single pulse; } t_p = 100 \mu s$$



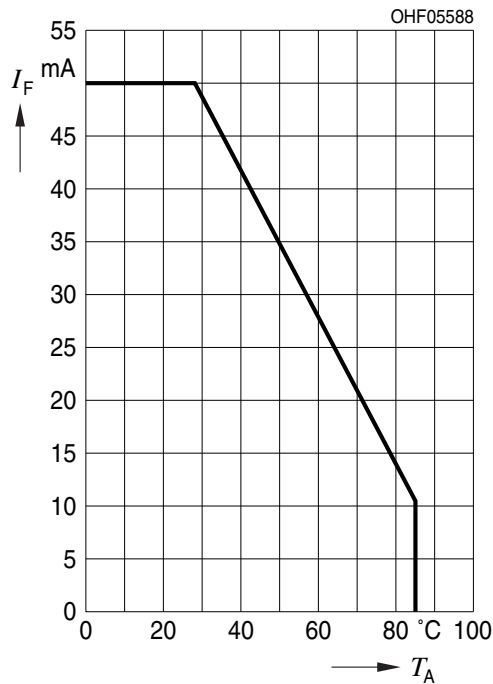
## Irradiance 9), 10)

$$E_e/E_e(50mA) = f(I_F); \text{ single pulse ; } t_p = 25 \mu s$$



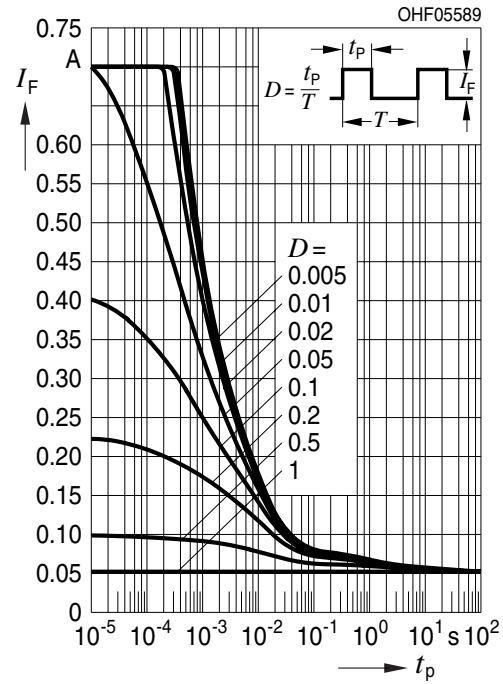
## Max. Permissible Forward Current

$$I_{F,max} = f(T_A); R_{th\,ja} = 420K / W$$



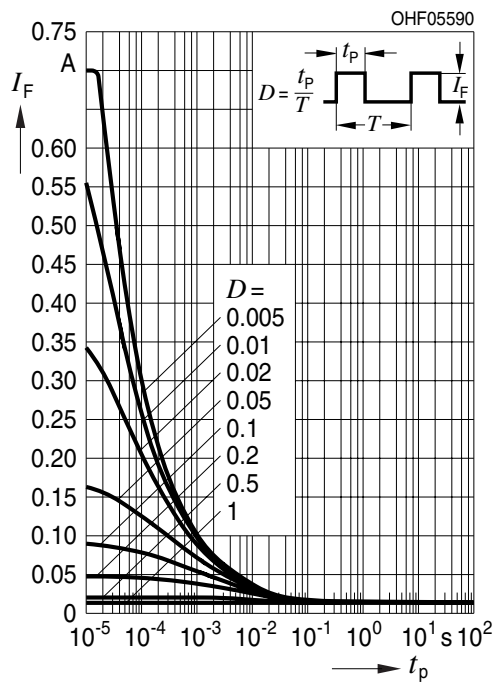
## Permissible Pulse Handling Capability

$$I_F = f(t_p); \text{ duty cycle } D = \text{parameter}; T_A = 25^\circ C$$

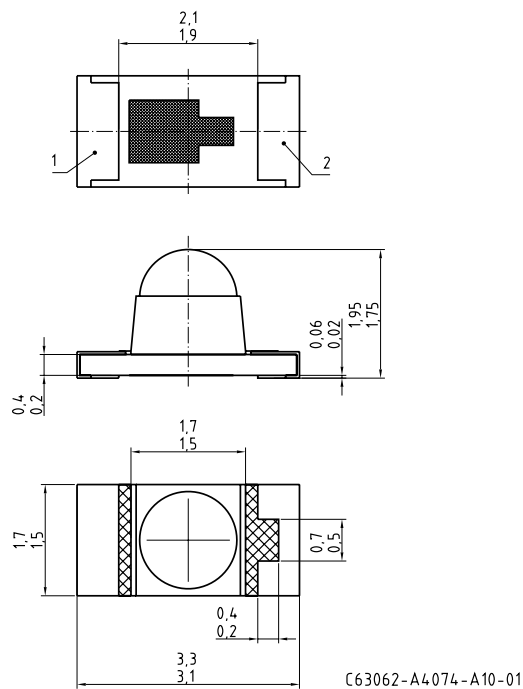


## Permissible Pulse Handling Capability

$$I_F = f(t_p); \text{ duty cycle } D = \text{parameter}; T_A = 85^\circ C$$



Dimensional Drawing <sup>11)</sup>



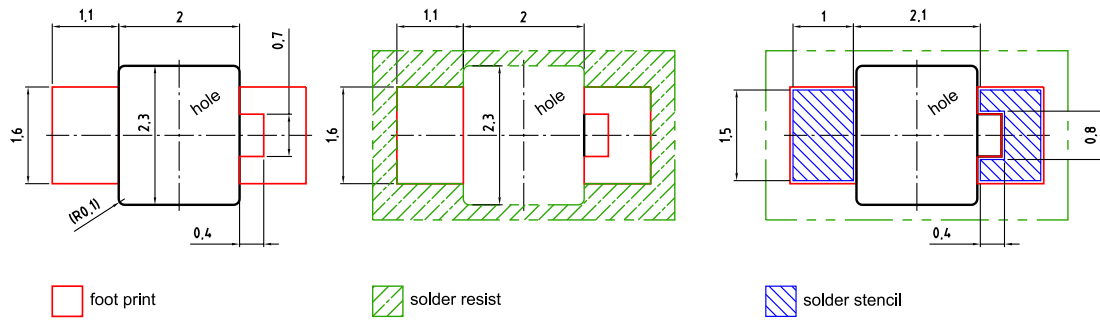
Further Information:

Approximate Weight: 8.0 mg

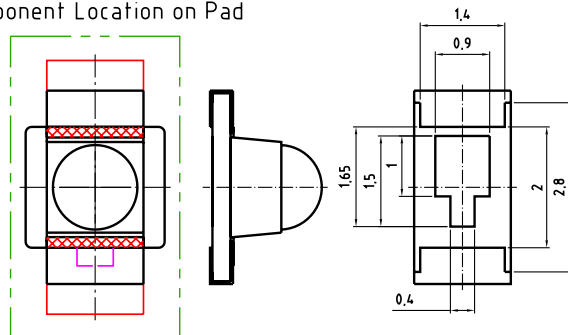
Package marking: Anode

| Pin | Description |
|-----|-------------|
| 1   | Cathode     |
| 2   | Anode       |

## Recommended Solder Pad <sup>11)</sup>



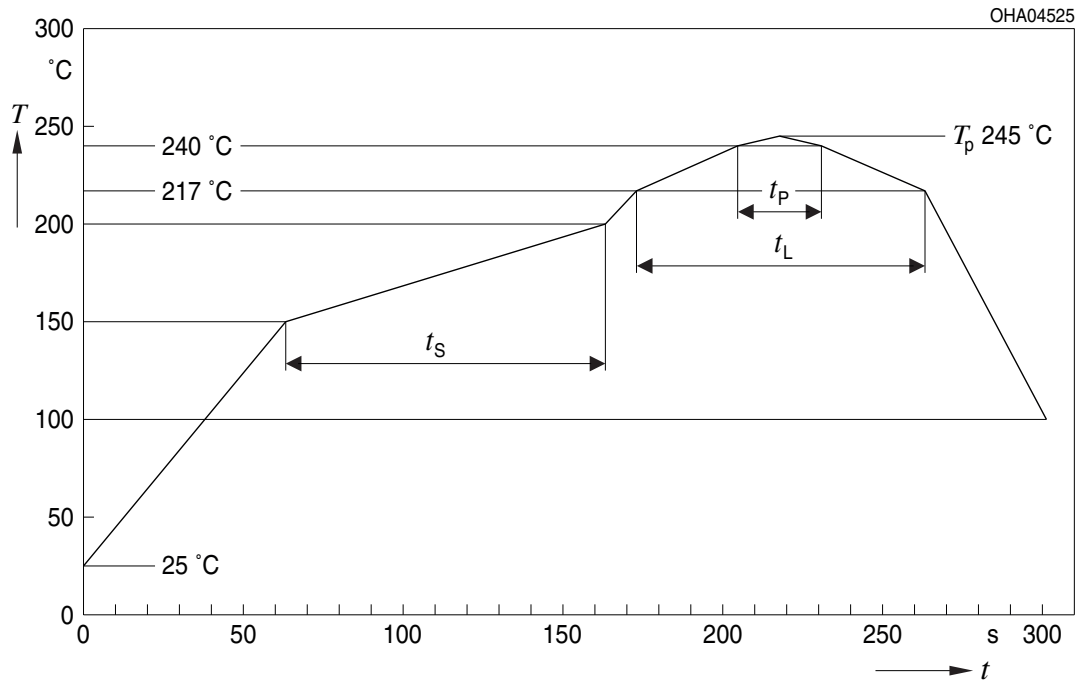
Component Location on Pad



E062 3010 165-03

## Reflow Soldering Profile

Product complies to MSL Level 3 acc. to JEDEC J-STD-020E

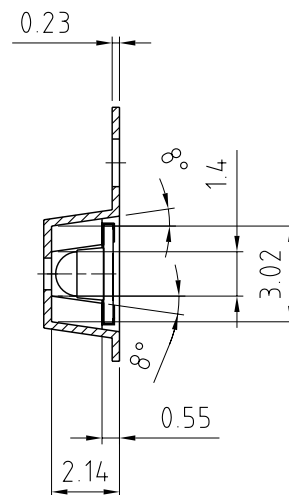
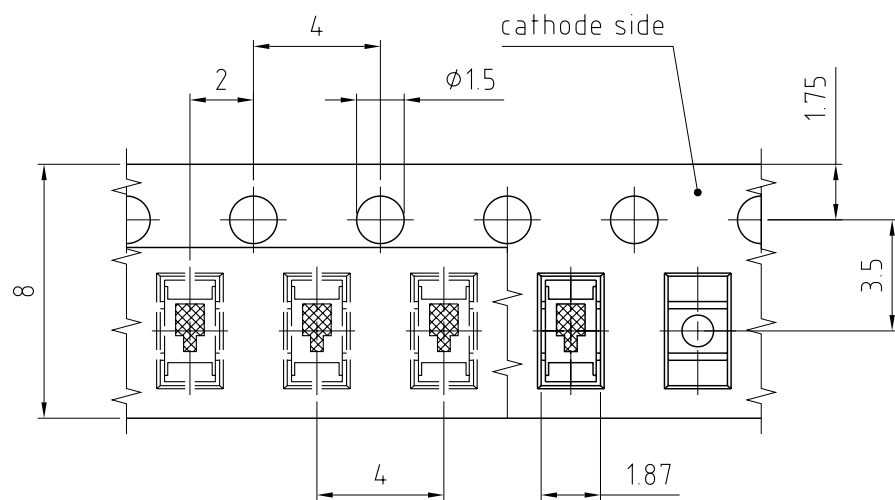


| Profile Feature                                                          | Symbol | Pb-Free (SnAgCu) Assembly |                |         | Unit               |
|--------------------------------------------------------------------------|--------|---------------------------|----------------|---------|--------------------|
|                                                                          |        | Minimum                   | Recommendation | Maximum |                    |
| Ramp-up rate to preheat <sup>*)</sup><br>25 °C to 150 °C                 |        |                           | 2              | 3       | K/s                |
| Time $t_s$<br>$T_{Smin}$ to $T_{Smax}$                                   | $t_s$  | 60                        | 100            | 120     | s                  |
| Ramp-up rate to peak <sup>*)</sup><br>$T_{Smax}$ to $T_p$                |        |                           | 2              | 3       | K/s                |
| Liquidus temperature                                                     | $T_L$  |                           | 217            |         | $^{\circ}\text{C}$ |
| Time above liquidus temperature                                          | $t_L$  |                           | 80             | 100     | s                  |
| Peak temperature                                                         | $T_p$  |                           | 245            | 260     | $^{\circ}\text{C}$ |
| Time within 5 °C of the specified peak<br>temperature $T_p - 5\text{ K}$ | $t_p$  | 10                        | 20             | 30      | s                  |
| Ramp-down rate*<br>$T_p$ to 100 °C                                       |        |                           | 3              | 6       | K/s                |
| Time<br>25 °C to $T_p$                                                   |        |                           |                | 480     | s                  |

All temperatures refer to the center of the package, measured on the top of the component

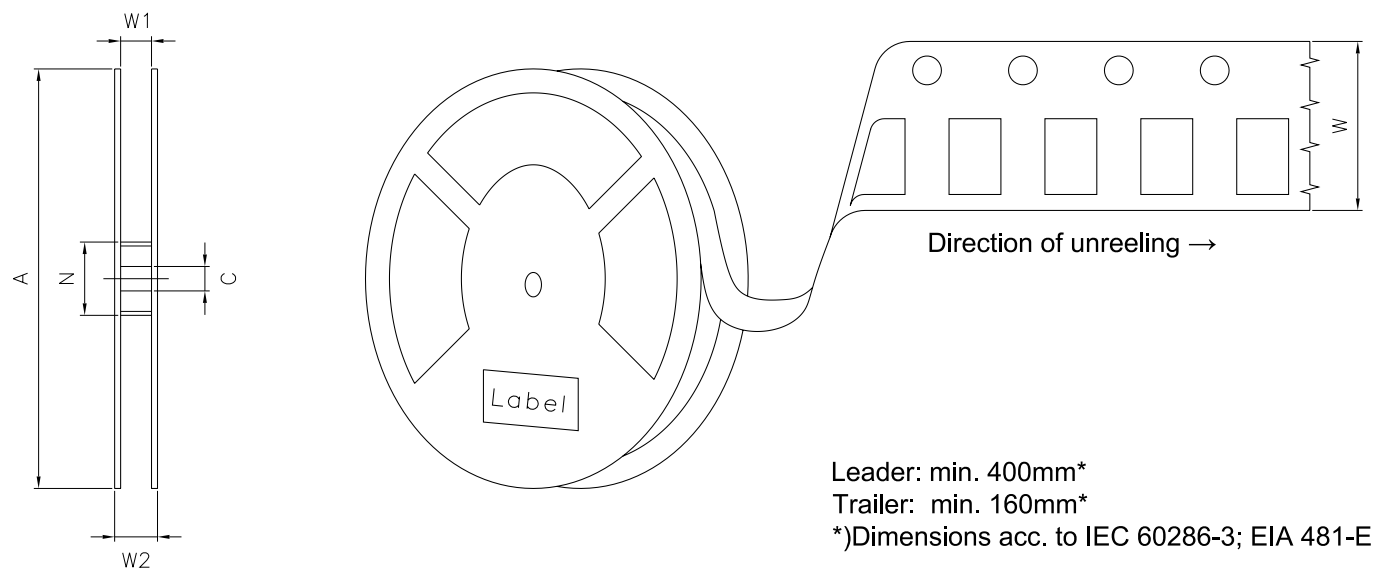
\* slope calculation  $DT/Dt$ :  $Dt$  max. 5 s; fulfillment for the whole T-range

## Taping <sup>11)</sup>



C63062-A4074-B2-02

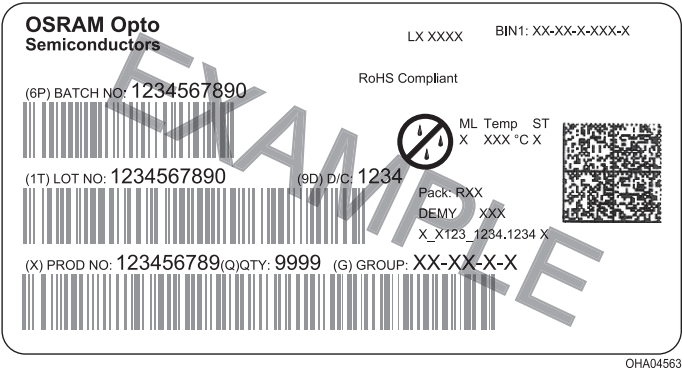
## Tape and Reel <sup>12)</sup>



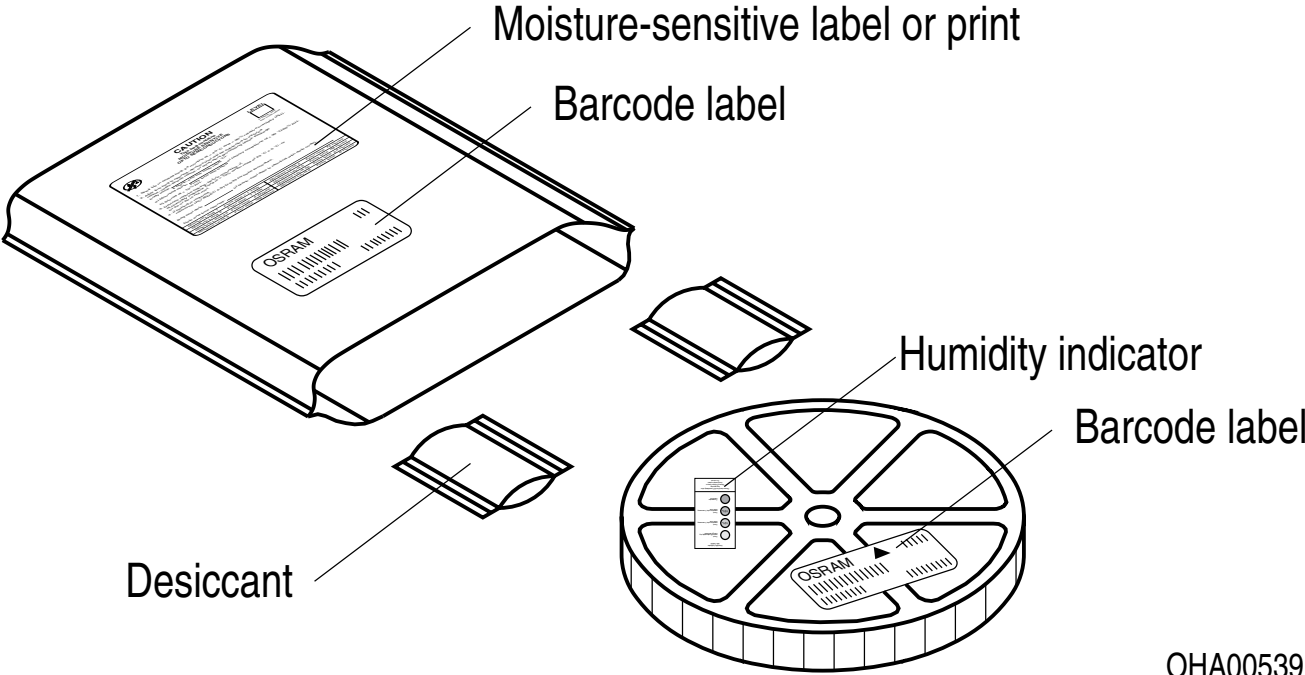
## Reel Dimensions

| A      | W                  | N <sub>min</sub> | W <sub>1</sub> | W <sub>2 max</sub> | Pieces per PU |
|--------|--------------------|------------------|----------------|--------------------|---------------|
| 180 mm | 8 + 0.3 / - 0.1 mm | 60 mm            | 8.4 + 2 mm     | 14.4 mm            | 2000          |

Barcode-Product-Label (BPL)



Dry Packing Process and Materials 11)



Moisture-sensitive product is packed in a dry bag containing desiccant and a humidity card according JEDEC-STD-033.

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## Notes

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet fall into the class **exempt group (exposure time 10000 s)**. Under real circumstances (for exposure time, conditions of the eye pupils, observation distance), it is assumed that no endangerment to the eye exists from these devices. As a matter of principle, however, it should be mentioned that intense light sources have a high secondary exposure potential due to their blinding effect. When looking at bright light sources (e.g. headlights), temporary reduction in visual acuity and afterimages can occur, leading to irritation, annoyance, visual impairment, and even accidents, depending on the situation.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit [www.osram-os.com/appnotes](http://www.osram-os.com/appnotes)

## Disclaimer

### Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on the OSRAM OS website.

### Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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## Glossary

- 1) **Irradiance:** Measured at a solid angle of  $\Omega = 0.1$  sr
- 2) **Brightness:** The brightness values are measured with a tolerance of  $\pm 11\%$ .
- 3) **Reverse Operation:** This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- 4) **Forward Voltage:** The forward voltages are measured with a tolerance of  $\pm 0.1$  V.
- 5) **Radiant intensity:** Measured at a solid angle of  $\Omega = 0.01$  sr
- 6) **Total radiant flux:** Measured with integrating sphere.
- 7) **Thermal resistance:** junction - soldering point, of the device only, mounted on an ideal heatsink (e.g. metal block)
- 8) **Thermal resistance:** junction - ambient, mounted on PC-board (FR4), padsize  $16 \text{ mm}^2$  each
- 9) **Typical Values:** Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 10) **Testing temperature:**  $T_A = 25^\circ\text{C}$  (unless otherwise specified)
- 11) **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with  $\pm 0.1$  and dimensions are specified in mm.
- 12) **Tape and Reel:** All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.

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## Revision History

| Version | Date       | Change                                                           |
|---------|------------|------------------------------------------------------------------|
| 1.4     | 2020-08-10 | Schematic Transportation Box<br>Dimensions of Transportation Box |
| 1.5     | 2021-09-30 | Brand                                                            |

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